

BGS12AL7-6

SPDT RF Switch

Data Sheet

Revision 2.1, 2009-12-09

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BGS12AL7-6 SPDT RF Switch

Revision History: 2009-12-09, Revision 2.1

Previous Revision: 2009-11-24, V2.0

Page	Subjects (major changes since last revision)
11	max. Values for Insertion Loss @ $T_A = -30\text{ }^{\circ}\text{C} \dots +85\text{ }^{\circ}\text{C}$

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Last Trademarks Update 2009-10-19

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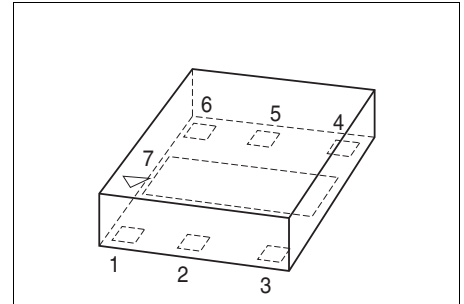
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1 Features

Main features:

- Low insertion loss
- High port-to-port-isolation
- Low harmonic generation
- On-chip control logic, only one control line required
- High ESD robustness
- No external components required
- General purpose switch for applications up to 3 GHz
- Small leadless package TSLP-7-6
- Lead and halogen free package (RoHS and WEEE compliant)



Description

The BGS12AL7-6 General Purpose RF MOS switch is designed to cover a broad range of applications from 30 MHz to 3 GHz. The symmetric design of its single pole double throw configuration, as shown in [Figure 1](#) offers high design flexibility. This single supply chip integrates on-chip CMOS logic driven by a simple, single-pin CMOS or TTL compatible control input signal. The 0.1 dB compression point exceeds the switch's maximum input power level of 21 dBm, resulting in linear performance at all signal levels. The RF switch has a very low insertion loss of 0.4 dB in the 1 GHz and 0.5 dB in the 2 GHz range.

Unlike GaAs technology, external DC blocking capacitors at the RF ports are only required if DC voltage is applied externally.

Product Name	Package	Chip	Marking
BGS12AL7-6	TSLP7-6	M4781	12

The BGS12AL7-6 RF switch is manufactured in Infineon's patented MOS technology, offering the performance of GaAs with the economy and integration of conventional CMOS including the inherent higher ESD robustness.

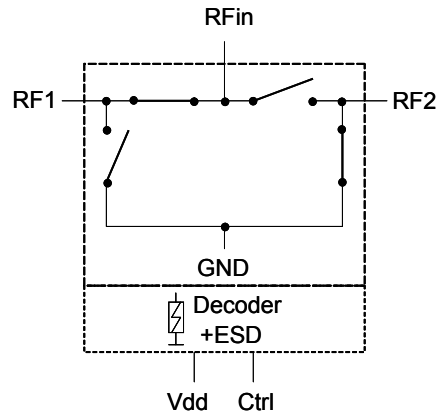


Figure 1 **Functional Diagram**

2 Maximum Ratings

Table 1 Maximum Ratings

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Storage temperature range	T_{stg}	-65	—	150	°C	—
DC Voltage at all pins to GND	V_{DC}	—	—	5	V	—
RF power max. at all RF ports	P_{IN}	—	—	24	dBm	—

ESD Capability

Human Body Model IEC61340-3-1	V_{ESD}	—	—	1000	V	—
Machine Model IEC61340-3-2		—	—	100		—
Charge Device Model JEDEC JESD22-C101D		—	—	1500		—

Table 2 Operation Ranges

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Ambient temperature	T_A	-30	—	85	°C	—
RF Frequency	f	0.03	—	3	GHz	—
Control voltage low	V_{CtrlL}	-0.3	—	0.3	V	—
Control voltage high	V_{CtrlH}	1.4	—	Vdd	V	—
Supply voltage ¹⁾	V_{dd}	2.4	—	3.6	V	—
Current consumption Vdd Pin (over temperature)	I_{Vdd}	80	—	350	μA	—
Current Consumption Vctrl Pin	I_{Ctrl}	—	—	30	μA	—
Power Range	P_{in}	—	—	—	dBm	—
(VSWR ∞: 1)		—	—	15		—
(VSWR 3: 1)		—	—	18		—
(VSWR 1: 1)		—	—	21		—

1) Supply voltage must be connected before Control Voltage

Attention: Stresses above the max. values listed here may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Maximum ratings are absolute ratings; exceeding only one of these values may cause irreversible damage to the integrated circuit.

3 Pin Description

Table 3 Pin Description

Pin No.	Name	Pin Type	Buffer Type	Function
1	RF2	I/O		RF Port 2 Out
2	GND	GND		Ground
3	RF1	I/O		RF Port 1 Out
4	Vdd	PWR		Supply Voltage
5	RFIN	I/O		RF Port In
6	CTRL	I		Control Pin
7	NC	NC		It is recommended to connect Pin 7 to Ground

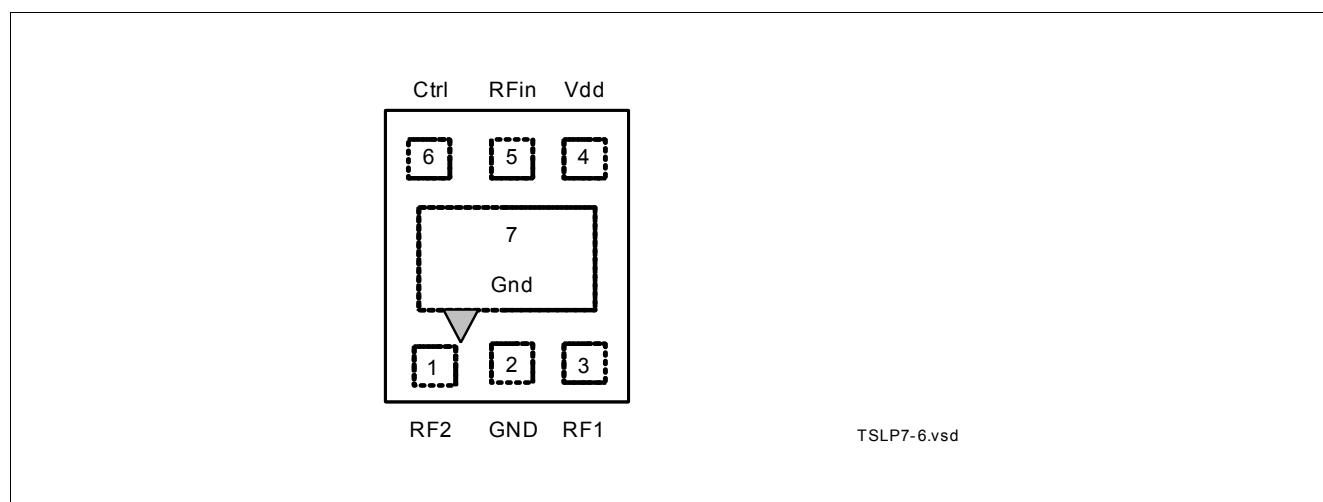


Figure 2 Pin Configuration (top view)

Table 4 Truth Table

Ctrl 1	RF 1	RF 2
0	1	0
1	0	1

4 Electrical Specifications

Test Conditions:

- Termination port impedance: $Z_0 = 50 \Omega$
- Temperature range: $T_A = -30^\circ\text{C} \dots +85^\circ\text{C}$
- Supply Voltage: $V_{dd} = 2.8 \text{ V}$
- $P_{in} = 15 \text{ dBm}$
- Across operating range of control voltages: $V_{Ctrl} = 1.4 \dots 2.8 \text{ V}$

Table 5 Electrical Characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Insertion Loss	IL	–	0.3 ¹⁾	0.5 ¹⁾	dB	$f = 0.1 \text{ GHz}$, $T_A = 25^\circ\text{C}$
		–	0.35	0.6	dB	$f = 1 \text{ GHz}$, $T_A = 25^\circ\text{C}$
		–	0.5	0.7	dB	$f = 2 \text{ GHz}$, $T_A = 25^\circ\text{C}$
		–	–	0.6 ¹⁾	dB	$f = 0.1 \text{ GHz}$
		–	–	0.7 ¹⁾	dB	$f = 1 \text{ GHz}$
		–	–	0.8 ¹⁾	dB	$f = 2 \text{ GHz}$
Return Loss	RL	–	30 ¹⁾	–	dB	$f = 0.1 \text{ GHz}$
		15	20	–	dB	$f = 1 \text{ GHz}$
		12	15	–	dB	$f = 2 \text{ GHz}$
Isolation RFin - RF1	$ISO_{RFin-RF1}$	–	50 ¹⁾	–	dB	$f = 0.1 \text{ GHz}$
		20	32	–	dB	$f = 1 \text{ GHz}$
		15	25	–	dB	$f = 2 \text{ GHz}$
Isolation RFin - RF2	$ISO_{RFin-RF2}$	–	50 ¹⁾	–	dB	$f = 0.1 \text{ GHz}$
		20	32	–	dB	$f = 1 \text{ GHz}$
		15	25	–	dB	$f = 2 \text{ GHz}$
Isolation RF1 - RF2	$ISO_{RF1-RF2}$	–	50 ¹⁾	–	dB	$f = 0.1 \text{ GHz}$
		24	32	–	dB	$f = 1 \text{ GHz}$
		15	25	–	dB	$f = 2 \text{ GHz}$
Isolation RF ports - Vdd, Vctrl	ISO_{RF-DC}	25	30 ¹⁾	–	dB	$f = 1 \text{ GHz}$
		15	20 ¹⁾	–	dB	$f = 2 \text{ GHz}$
Harmonic Generation up to 12.75 GHz	P_{Harm}	–	-75 ¹⁾	-50	dBm	$f = 1 \text{ GHz}$
		–	-80 ¹⁾	-50	dBm	$f = 2 \text{ GHz}$
On Switching Time (10-90%) RF	t_{on}	–	3 ¹⁾	5	μs	$f = 1 \text{ GHz}$
Off Switching Time (10-90%) RF	t_{off}	–	0.5 ¹⁾	5	μs	$f = 1 \text{ GHz}$
Current Consumption at Vdd Pin	I_{dd}	–	140	–	μA	–
Input 0.1 dB compression	$P_{0.1dB}$	21 ¹⁾	–	–	dBm	$f = 1 \text{ GHz}$

1) Not measured in production, verified by design

5 Measurement Results

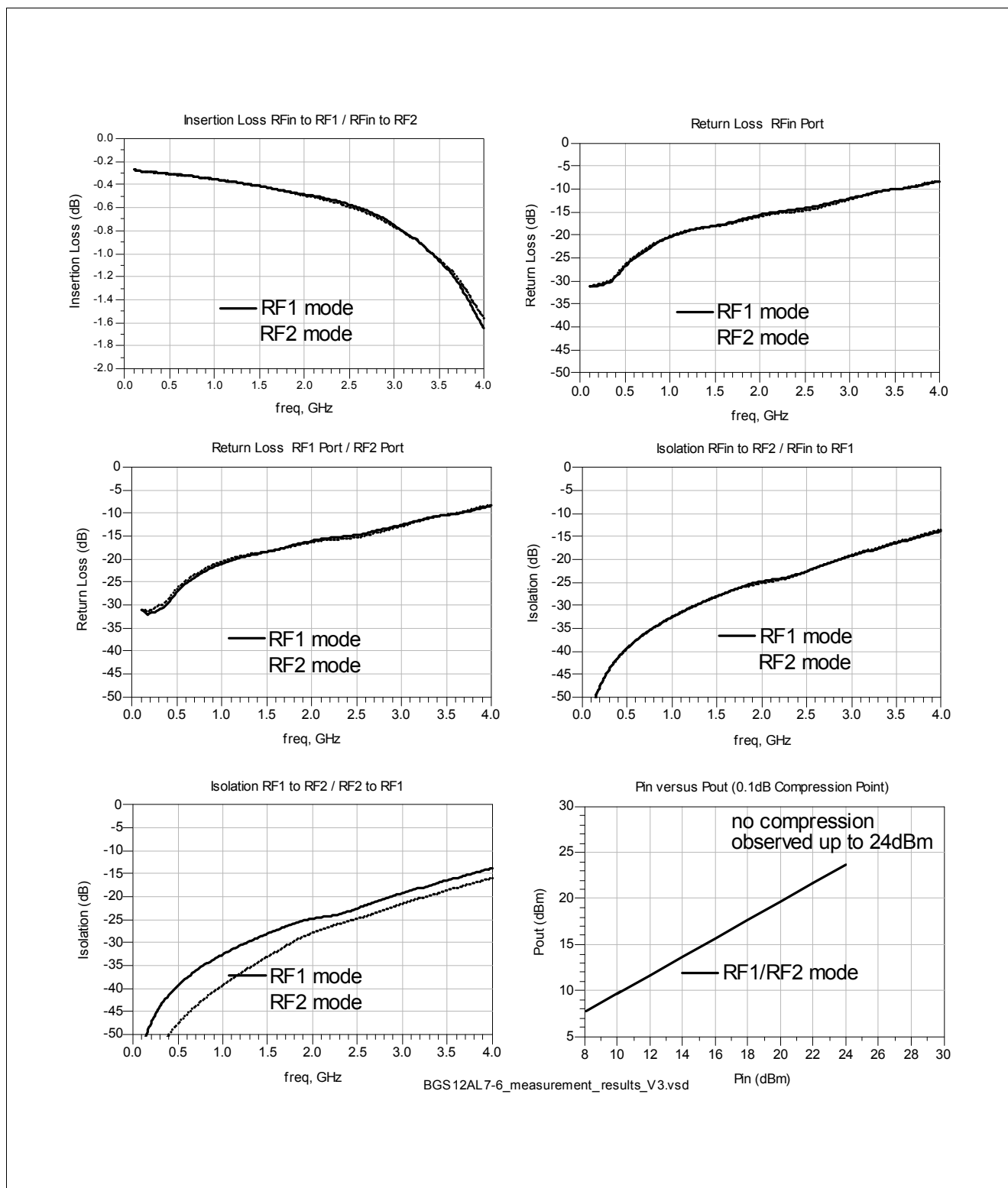


Figure 3 Measurement Results (@ $T = 25^{\circ}\text{C}$)

Application Board

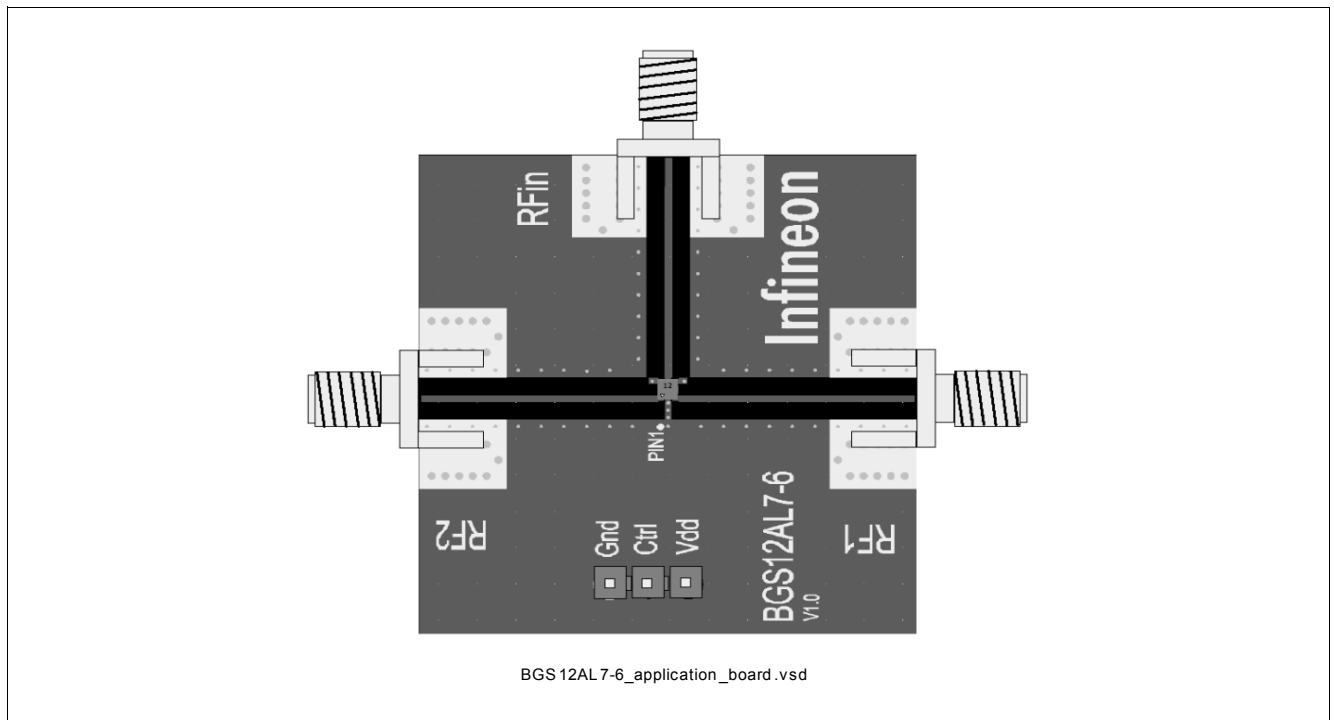


Figure 4 Application Board: No External Components Necessary

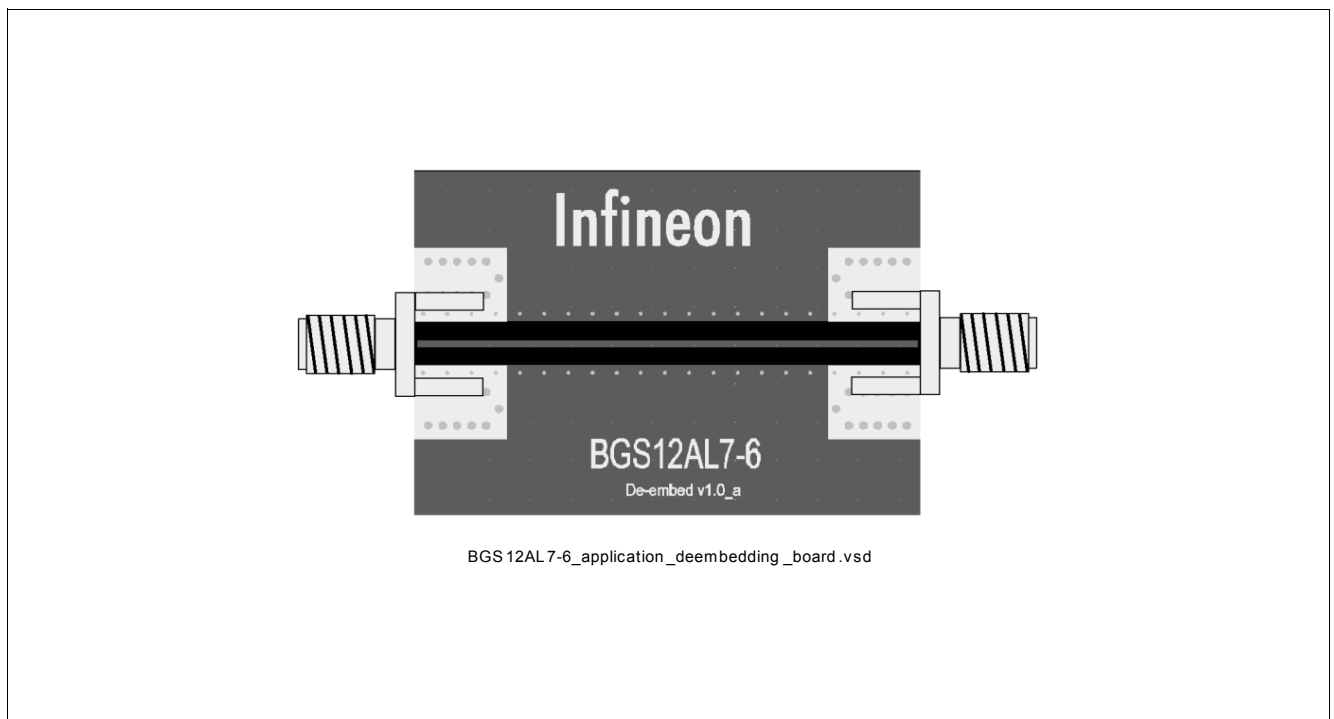


Figure 5 Deembedding Board

6 Package Outlines

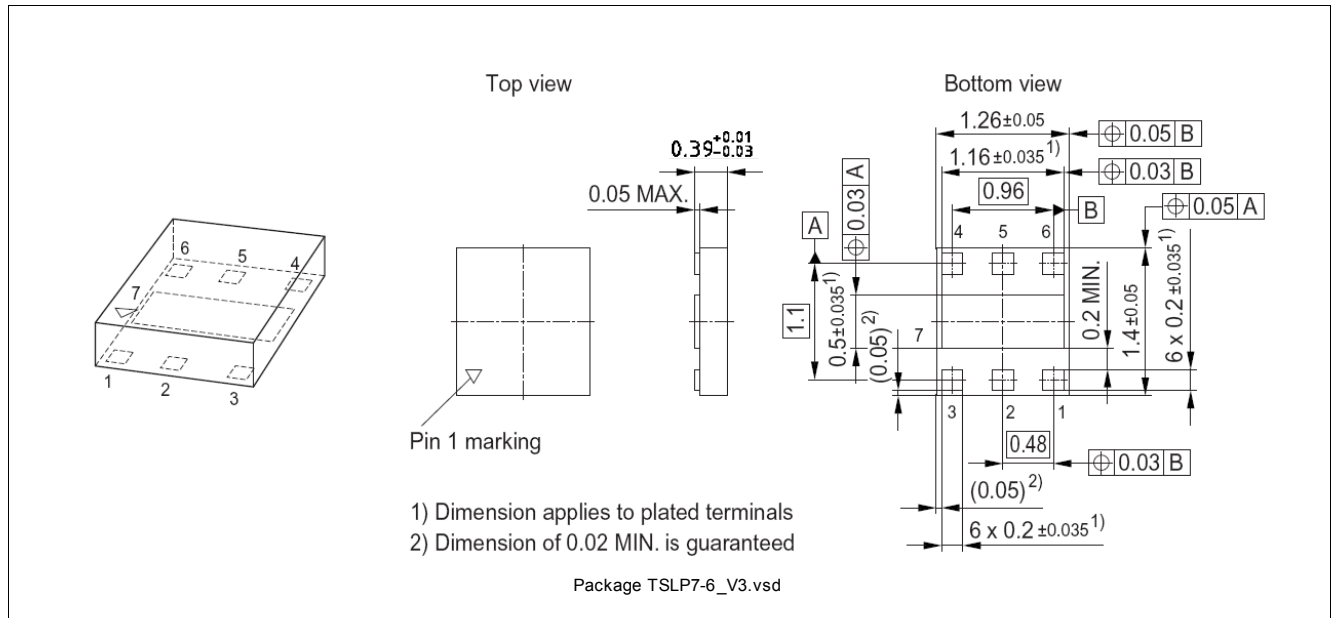


Figure 6 Package TSLP7-6

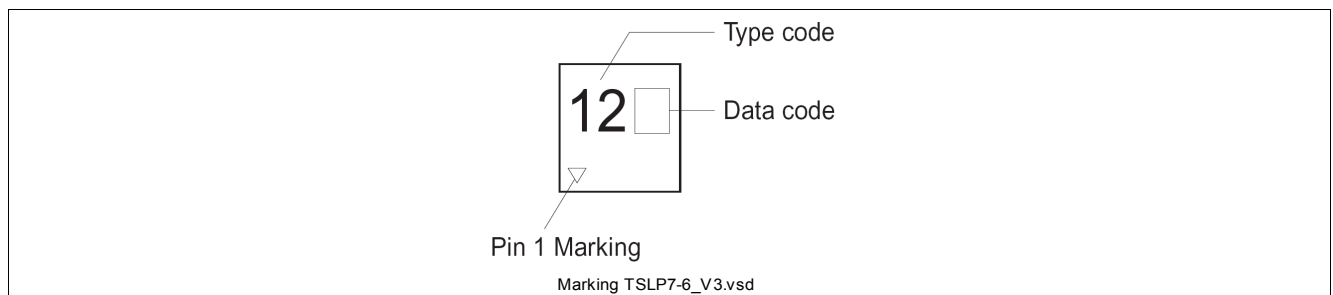


Figure 7 Marking Info

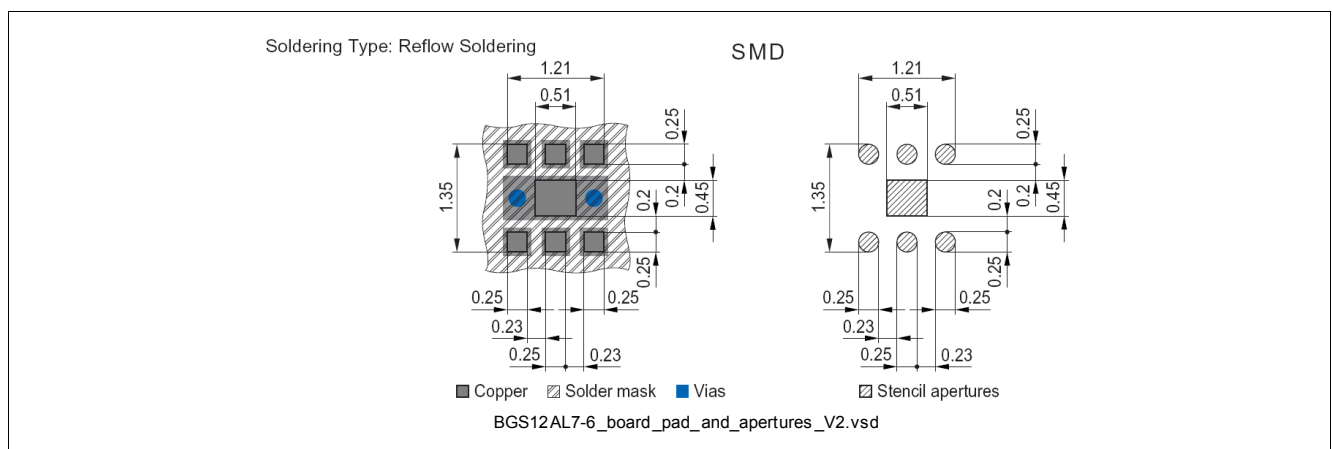


Figure 8 Board pad (SMD) & Apertures

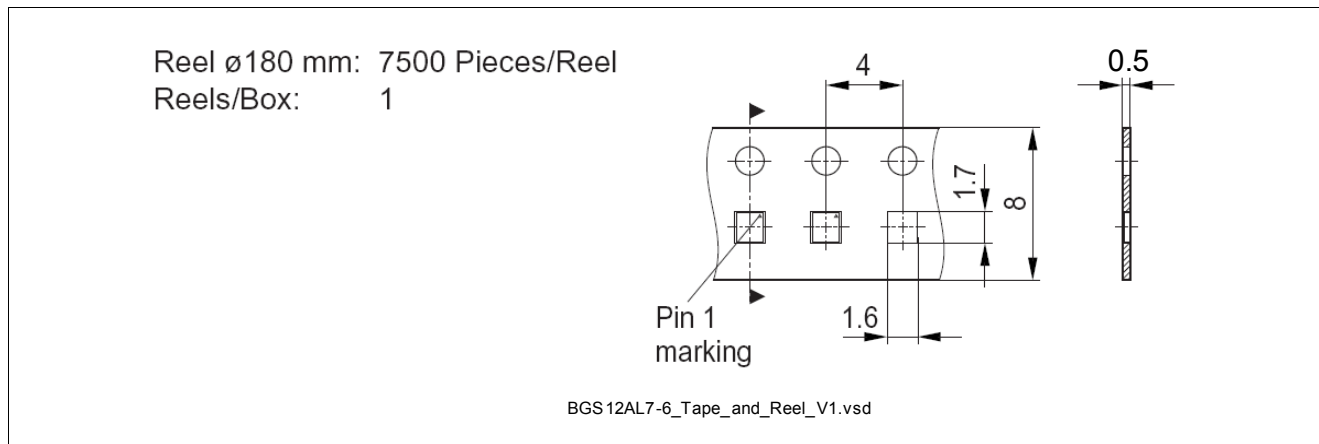


Figure 9 Tape and Reel

Dimensions in mm

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www.infineon.com



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